
Silicon Compatible Materials, Processes, and Technologies for Advanced Integrated Circuits and Emerging Applications 6

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Sponsoring Division:



Electronics and Photonics



Published by

The Electrochemical Society

65 South Main Street, Building D
Pennington, NJ 08534-2839, USA

tel 609 737 1902

fax 609 737 2743

www.electrochem.org

ecstransactions™

Vol. 72, No. 4

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Published by:

The Electrochemical Society
65 South Main Street
Pennington, New Jersey 08534-2839, USA

Telephone 609.737.1902
Fax 609.737.2743
e-mail: ecs@electrochem.org
Web: www.electrochem.org

ISSN 1938-6737 (online)
ISSN 1938-5862 (print)
ISSN 2151-2051 (cd-rom)

ISBN 978-1-62332-356-1 (CD-ROM)
ISBN 978-1-60768-714-6 (PDF)

Printed in the United States of America.

ECS Transactions, Volume 72, Issue 4
Silicon Compatible Materials, Processes, and Technologies for Advanced
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Table of Contents

<i>Preface</i>	<i>iii</i>
 Chapter 1 Keynote 	
(Keynote) Challenges of 10 nm and 7 nm CMOS for Server and Mobile Applications <i>R. Divakaruni, V. Narayanan</i>	3
 Chapter 2 New Device Architectures 	
(Invited) Challenges and Solutions for Future Internet-of-Things Semiconductor Technologies <i>J. K. Schaeffer III</i>	17
Introduction of a High Selectivity Etching Process with Advanced SiN _x Etch Gas in the Fabrication of FinFET Structures <i>T. Kojiri, T. Suwa, K. Hashimoto, A. Teramoto, R. Kuroda, S. Sugawa</i>	23
(Invited) Vertical Nanowire FET Integration and Device Aspects <i>A. Veloso, E. Altamirano-Sánchez, S. Brus, B. T. Chan, M. Cupak, M. Dehan, C. Delvaux, K. Devriendt, G. Eneman, M. Ercken, T. Huynh-Bao, T. Ivanov, P. Matagne, C. Merckling, V. Paraschiv, S. Ramesh, E. Rosseel, L. Rynders, A. Sibaja-Hernandez, S. Suhard, Z. Tao, E. Vecchio, N. Waldron, D. Yakimets, K. De Meyer, D. Mocuta, N. Collaert, A. Thean</i>	31
(Invited) Evaluation of Stacked Nanowires Transistors for CMOS: Performance and Technology Opportunities <i>L. Gaben, S. Barraud, M. P. Samson, M. A. Jaud, S. Martinie, O. Rozeau, J. Lacord, C. Arvet, C. Vizioz, J. Bustos, J. A. Dallery, S. Pauliac, V. Balan, C. Euvrard-Colnat, C. Perrot, V. Loup, P. Besson, J. M. Hartmann, S. Monfray, F. Boeuf, T. Skotnicki, F. Balestra, M. Vinet</i>	43

Chapter 3

High Voltage Electronics/Photonics

- (Invited) Effect of Low Carbon Concentration on Bulk Lifetime of Silicon Crystal 57
M. Higasa, Y. Nagai, S. Nakagawa, K. Kashima
- (Invited) Intrinsic Reliability Assessment of 650V Rated AlGaIn/GaN Based Power Devices: An Industry Perspective 65
P. Moens, A. Banerjee, A. Constant, P. Coppens, M. Caesar, Z. Li, S. Vandeweghe, F. Declercq, B. Padmanabhan, W. Jeon, J. Guo, A. Salih, M. Tack, M. Meneghini, S. Dalcanale, A. Tajilli, G. Meneghesso, E. Zanoni, M. Uren, I. Chatterjee, S. Karboyan, M. Kuball

Chapter 4

FEOL/BEOL: Materials and Processes

- (Invited) TmSiO as a CMOS-Compatible High-k Dielectric 79
E. Dentoni Litta, P. E. Hellström, M. Östling
- Low Leakage Current Al₂O₃ Metal-Insulator-Metal Capacitors Formed By Atomic Layer Deposition at Optimized Process Temperature and O₂ Post Deposition Annealing 91
Y. Koda, H. Sugita, T. Suwa, R. Kuroda, T. Goto, A. Teramoto, S. Sugawa
- (Invited) Low-Temperature Microwave-Based Plasma Oxidation of Ge and Oxidation of Silicon Followed by Plasma Nitridation 101
W. Lerch, T. Schick, N. Sacher, W. Kegel, J. Niess, M. Czernohorsky, S. Riedel
- (Invited) The (R)Evolution of the Junctionless Transistor 115
R. Duffy
- Formation of Low-Resistivity Metal/Germanium Contact with Ultra-Thin Interlayer and Plasma Oxidation for n-Channel Germanium FET 127
G. S. Kim, S. H. Kim, J. Park, S. W. Kim, H. Y. Yu
- (Invited) Pattern and Emissivity Insensitive Dopant Activation and Silicide Contact Formation Annealing in a Hot Wall Rapid Thermal Annealing System 131
W. S. Yoo

Height Uniformity of Micro-Bumps Electroplated on Thin Cu Seed Layers <i>L. Yang, J. Slabbekoorn, M. Honore, K. Stiers, H. Struyf, P. M. Vereecken, A. Radisic</i>	145
---	-----

Vapor Phase Self-Assembled Monolayers for CMOS BEOL Barrier Layers <i>T. R. Naik, M. Ravikanth, V. R. Rao</i>	153
--	-----

Chapter 5 Memory Devices and III-V Photonics

(Invited) Graphene Plane Electrode for Low Power 3D Resistive Random Access Memory <i>S. Lee, J. Sohn, Z. Jiang, H. Y. Chen, H. S. P. Wong</i>	159
--	-----

(Invited) Role of Interfaces in Achieving Self-Compliance Controlled Resistive Random Access Memory Devices for Low-Power Embedded Applications <i>R. Jha, W. Lu, W. Chen</i>	165
---	-----

(Invited) III-V / Si Integration for Photonics <i>J. P. Reithmaier, M. Benyoucef</i>	171
---	-----

Chapter 6 Poster Session

Development of Characterization Platform Dedicated to Bio-Inspired Objects at the Nanoscale <i>C. Carmignani, A. Thuairre, A. Rongier, L. Altamura, C. Brun, P. Reynaud, E. Rolland, N. David, P. Rannou, V. Forge, T. Ernst, S. Cheramy</i>	183
--	-----

Simulation of the Germanium-Tin Tunneling Field-Effect Transistors with a Ge Cap Layer: Improved Subthreshold Swing and I_{on}/I_{off} Ratio <i>L. Liu, R. Liang, J. Wang, J. Xu</i>	191
--	-----

Comprehensive Characterization of Dual Implanted Silicon after Electrical Activation Annealing <i>W. S. Yoo, B. S. Jeon, S. D. Kim, T. Ishigaki, K. Kang</i>	199
--	-----

Effect of Substrate Type on CoSi ₂ Formation in Rapid Thermal Annealing <i>E. J. Kim, J. Y. Lee, S. D. Kim, H. S. Song, S. J. Yeom, T. Ishigaki, K. Kang, W. S. Yoo</i>	211
High Dopant Activation and Diffusion Suppression of Phosphorus in Ge Crystal with High-Temperature Implantation By Two-Step Microwave Annealing <i>T. L. Shih, W. H. Lee</i>	219
Wet Chemical Etching Behavior Investigation for CMOS Shallow Trench Isolation (STI) Shape Control <i>H. Tai, P. C. Chang, H. W. Ho, H. Y. Liao, M. C. Lu, T. H. Ying</i>	227
Analysis of the Retention Characteristic in Three dimensional Junction-less Charge Trapping Memory <i>D. Jiang, Z. Xia, L. Jin, X. Zou, Y. Zhang, Z. Tang, X. Li, Z. Huo</i>	233
High-K Metal-Gate Nanowire Junctionless FinFET with Nickel Silicide by Microwave Annealing <i>W. T. Tsai, Y. H. Lin</i>	239
Novel Oxidants and Sources of Nitrogen for Atomic Layer Deposition <i>D. Alvarez Jr., J. Spiegelman, E. Heinlein, R. Holmes, C. Ramos, M. Leo, S. Webb</i>	243
Crystallinity Evaluation of Low Temperature Polycrystalline Silicon Thin Film Using UV/Visible Raman Spectroscopy <i>R. Yokogawa, K. Takahashi, K. Komori, Y. Hirota, N. Sawamoto, A. Ogura</i>	249
Fabrication of Graphene/Porous Silicon Nitride Material for Field-Effect Transistors <i>D. Ge, D. Qian, G. Chen, L. Zhang, N. Ren</i>	257
High Performance Tri-Gate Germanium-on-insulator Based Junctionless Nanowire Transistors <i>C. Sun, R. R. Liang, J. Wang, J. Xu</i>	263
Hot-Wire Chemical Vapour Deposition for Silicon Nitride Waveguides <i>T. Domínguez Bucio, A. Tarazona, A. Z. Khokhar, G. Z. Mashanovich, F. Y. Gardes</i>	269

Chapter 7
A Historical Perspective on Integrated Circuits

(Invited) Transistors, Integrated Circuits and Nano-Technology: A Historical Review <i>H. R. Huff</i>	275
--	-----

Chapter 8
Alternate Channel Materials and Devices

(Invited) Rapid In-Situ Carbon and Oxygen Cleaning of In _{0.53} Ga _{0.47} As(001) and Si _{0.5} Ge _{0.5} (110) Surfaces via a H ₂ RF Downstream Plasma <i>S. Wolf, M. Edmonds, X. Jiang, R. Droopad, N. Yoshida, L. Dong, R. Galatage, S. Siddiqui, B. Sahu, A. Kummel</i>	291
Effect of Post Plasma Oxidation on Ge Gate Stacks Interface Formation <i>S. Mukhopadhyay, S. Mitra, Y. M. Ding, K. L. Ganapathi, D. Misra, N. Bhat, K. Tapily, R. D. Clark, S. Consiglio, C. S. Wajda, G. J. Leusink</i>	303
(Invited) CMOS Compatible High Performance IIIV Devices: Opportunities and Challenges <i>Y. Sun, K. T. Shiu, C. W. Cheng, A. Majumdar, R. Bruce, J. B. Yau, D. Farmer, Y. Zhu, M. Hopstaken, M. M. Frank, T. Ando, K. T. Lee, J. Rozen, D. K. Sadana, V. Narayanan, R. T. Mo, E. Leobandung</i>	313
Source/Drain Contact Resistance Reduction through Al-Doped ZnO Interlayer to Metal-Interlayer-GaAs Contact Structure <i>S. H. Kim, G. S. Kim, S. W. Kim, H. Y. Yu</i>	321
Study of Electrostatics and Transport Properties of Multigate Graded Nanowire Channel MOSFETs <i>Q. D. M. Khosru, S. U. Z. Khan, K. Datta</i>	325
Determination of Antiphase Domain Boundary Annihilation Rate in GaAs on Si(001) and the Influence of MOCVD Growth Temperature <i>C. S. C. Barrett, T. P. Martin, X. Y. Bao, P. Martin, E. Sanchez, K. S. Jones</i>	335
Author Index	341